Taiwan

# 10A, 35V - 200V Schottky Barrier Rectifier

#### FEATURES

TAIWAN

• AEC-Q101 qualified available

EMICONDUCTOR

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

#### **MECHANICAL DATA**

- Case: TO-220AC
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.88g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I <sub>F</sub>	10	А		
V <sub>RRM</sub>	35 - 200	V		
I <sub>FSM</sub>	150	А		
T <sub>J MAX</sub>	150	°C		
Package	TO-220AC			
Configuration	Single	die		







ABSOLUTE MAXIMUM I	RATINGS (	$T_A = 25^{\circ}C$	C unless	otherwis	se noted)	)				
PARAMETER	SYMBOL	MBR 1035	MBR 1045	MBR 1050	MBR 1060	MBR 1090	MBR 10100	MBR 10150	MBR 10200	וואט
Marking code on the device		MBR 1035	MBR 1045	MBR 1050	MBR 1060	MBR 1090	MBR 10100	MBR 10150	MBR 10200	
Repetitive peak reverse voltage	V <sub>RRM</sub>	35	45	50	60	90	100	150	200	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	24	31	35	42	63	70	105	140	V
Forward current	۱ <sub>۶</sub>		10						Α	
Surge peak forward current 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>	150					А			
Peak repetitive forward current (Rated V <sub>R</sub> , Square Wave, 20KHz)	I <sub>FRM</sub>	20					A			
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1 0.5					Α			
Voltage rate of change (Rated $V_R$ )	dV/dt				10,	000				V/µs



<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)										
PARAMETER	SYMBOL	MBR 1035	MBR 1045	MBR 1050	MBR 1060	MBR 1090	MBR 10100	MBR 10150	MBR 10200	UNIT
Junction temperature	TJ	1000	1040	1000		+150	10100	10100	10200	°C
Storage temperature	T <sub>STG</sub>	-55 to +175			°C					

Notes:

1.  $tp = 2.0\mu s$ , 1.0KHz

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case resistance	R <sub>eJC</sub>	3	°C/W

ELECTRICAL SPECIFI	CATIONS	$T_A = 25^{\circ}C$ unless other	erwise noted)			
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBR1035 MBR1045	I <sub>F</sub> = 10A, T <sub>J</sub> = 25°C		-	0.70	V
	MBR1050 MBR1060			-	0.80	V
	MBR1090 MBR10100	IF - 10A, 1J - 20 0		-	0.85	V
Forward voltage <sup>(1)</sup>	MBR10150 MBR10200		V <sub>F</sub>	-	1.05	V
Forward voltage	MBR1035 MBR1045		vF	-	0.57	V
	MBR1050 MBR1060			-	0.70	V
	MBR1090 MBR10100			-	0.71	V
	MBR10150 MBR10200			-	-	V
MBR <sup>7</sup> MBR <sup>7</sup> MBR <sup>7</sup> MBR <sup>7</sup> MBR <sup>7</sup> MBR <sup>7</sup> MBR1	MBR1035 MBR1045 MBR1050 MBR1060 MBR1090 MBR10100 MBR10150	T <sub>J</sub> = 25°C		-	100	μA
Reverse current @ rated $V_R^{(2)}$	MBR1035 MBR1045		I <sub>R</sub>	-	15	mA
	MBR1050 MBR1060	Т <sub>.1</sub> = 125°С		-	10	mA
	MBR1090 MBR10100 MBR10150 MBR10200	1 J= 125 C		-	6	mA

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms



## ORDERING INFORMATION

ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING
MBR10x	TO-220AC	50 / Tube
MBR10xH	TO-220AC	50 / Tube

Notes:

1. "x" defines voltage from 35V(MBR1035) to 200V(MBR10200)

2. "H" means AEC-Q101 qualified



10

REVERSE VOLTAGE (V)

**Fig.4 Typical Forward Characteristics** 

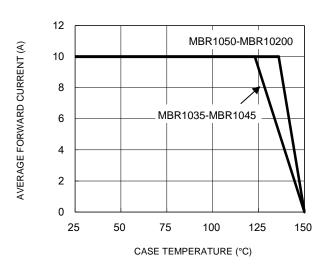
100

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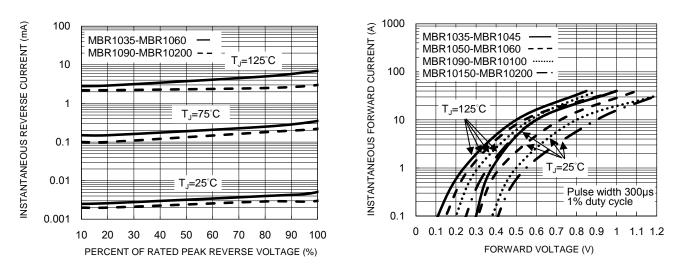
#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

Fig.1 Forward Current Derating Curve



**Fig.3 Typical Reverse Characteristics** 



10000

1000

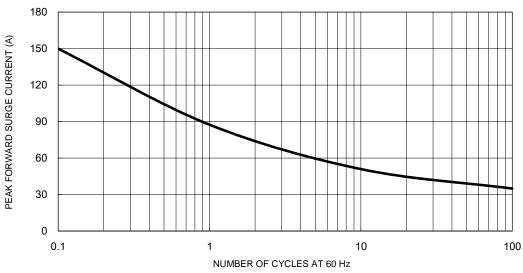
100

0.1

f=1.0MHz Vsig=50mVp-p

1

CAPACITANCE (pF)



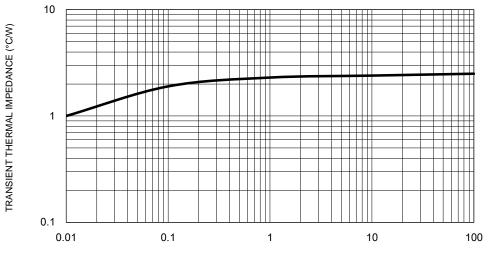
#### Fig.5 Maximum Non-Repetitive Forward Surge Current

Fig.2 Typical Junction Capacitance



### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



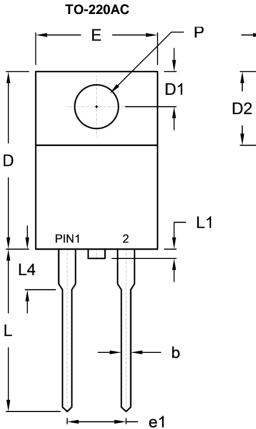
#### Fig.6 Typical Transient Thermal Impedance

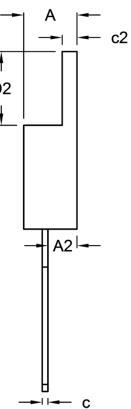
PULSE DURATION (s)

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**5** TAIWAN SEMICONDUCTOR





DIM.	Unit	(mm)	Unit (	(inch)
	Min.	Max.	Min.	Max.
A	4.42	4.76	0.174	0.187
A2	2.20	2.80	0.087	0.110
b	0.68	0.94	0.027	0.037
с	0.35	0.64	0.014	0.025
c2	1.14	1.40	0.045	0.055
D	14.60	16.00	0.575	0.630
D1	2.62	3.44	0.103	0.135
D2	5.84	6.86	0.230	0.270
E	-	10.50	-	0.413
e1	4.95	5.20	0.195	0.205
L	13.19	14.79	0.519	0.582
L1	0.00	1.60	0.000	0.063
L4	2.80	4.20	0.110	0.165
Р	3.54	4.00	0.139	0.157

#### **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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